RENESAS 2SA1084, 2SA1085

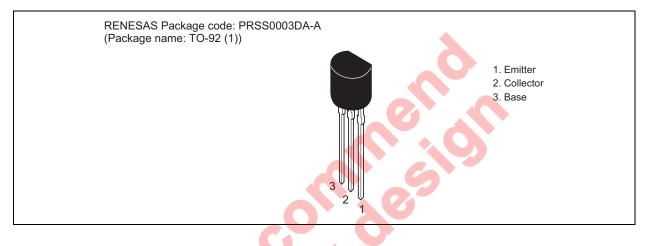
Silicon PNP Epitaxial

REJ03G0635-0300 (Previous ADE-208-1007A) Rev.3.00 Aug.10.2005

Application

Low frequency low noise amplifier

Outline



Absolute Maximum Ratings

| | | | | $(Ta = 25^{\circ}C)$ |
|------------------------------|------------------|-------------|-------------|----------------------|
| ltem 🔶 | Symbol | 2SA1084 | 2SA1085 | Unit |
| Collector to base voltage | V _{CBO} | -90 | -120 | V |
| Collector to emitter voltage | V _{CEO} | -90 | -120 | V |
| Emitter to base voltage | V _{EBO} | -5 | -5 | V |
| Collector current | Ic | -100 | -100 | mA |
| Emitter current | Ι _Ε | 100 | 100 | mA |
| Collector power dissipation | Pc | 400 | 400 | mW |
| Junction temperature | Tj | 150 | 150 | °C |
| Storage temperature | Tstg | –55 to +150 | -55 to +150 | ٥°C |



Electrical Characteristics

 $(Ta = 25^{\circ}C)$

| | | 2SA1084 | | 2SA1085 | | | | | |
|---------------------------|--------------------------------|---------|------|---------|------|------|------|------|------------------------------------|
| ltem | Symbol | Min | Тур | Max | Min | Тур | Max | Unit | Test conditions |
| Collector to base | V _{(BR)CBO} | -90 | _ | _ | -120 | _ | _ | V | $I_{C} = -10 \ \mu A, I_{E} = 0$ |
| breakdown voltage | | | | | | | | | |
| Collector to emitter | V _{(BR)CEO} | -90 | _ | — | -120 | _ | — | V | $I_{\rm C} = -1 {\rm mA},$ |
| breakdown voltage | | | | | | | | | R _{BE} = ∞ |
| Emitter to base | V _{(BR)EBO} | -5 | _ | — | -5 | _ | — | V | $I_E = -10 \ \mu A, \ I_C = 0$ |
| breakdown voltage | | | | | | | | | |
| Collector cutoff current | I _{CBO} | _ | — | -0.1 | | _ | -0.1 | μΑ | $V_{CB} = -50 \text{ V}, I_E = 0$ |
| Emitter cutoff current | I _{EBO} | _ | _ | -0.1 | _ | _ | -0.1 | μΑ | $V_{EB} = -2 V, I_{C} = 0$ |
| DC current transfer ratio | h _{FE} * ¹ | 250 | _ | 800 | 250 | | 800 | | $V_{CE} = -12 V,$ |
| | | | | | | | | | $I_{\rm C} = -2 \text{ mA}$ |
| Collector to emitter | V _{CE(sat)} | _ | _ | -0.2 | _ | _ | -0.2 | V | $I_{\rm C} = -10 {\rm mA},$ |
| saturation voltage | | | | | | | | | $I_B = -1 \text{ mA}$ |
| Base to emitter voltage | V _{BE} | | -0.6 | — | — | -0.6 | | V | $V_{CE} = -12 V,$ |
| | | | | | | | | | $I_{\rm C} = -2 \text{ mA}$ |
| Gain bandwidth product | f⊤ | _ | 90 | — | | 90 | - | MHz | $V_{CE} = -12 V$, |
| | | | | | | | | | $I_{\rm C} = -2 \text{ mA}$ |
| Collector output | Cob | _ | 3.5 | — | — | 3.5 | — | pF | $V_{CB} = -10 \text{ V}, I_E = 0,$ |
| capacitance | | | | | | | | | f = 1 MHz |
| Noise voltage referred to | en | _ | 0.5 | — | | 0.5 | | nV/ | $V_{CE} = -6V$, |
| input | | | | | | | | √Hz | $I_{\rm C} = -10 {\rm mA},$ |
| | | | | | | | | | f = 1 kHz, |
| | | | | | | | | | $R_g = 0$, $\Delta f = 1Hz$ |

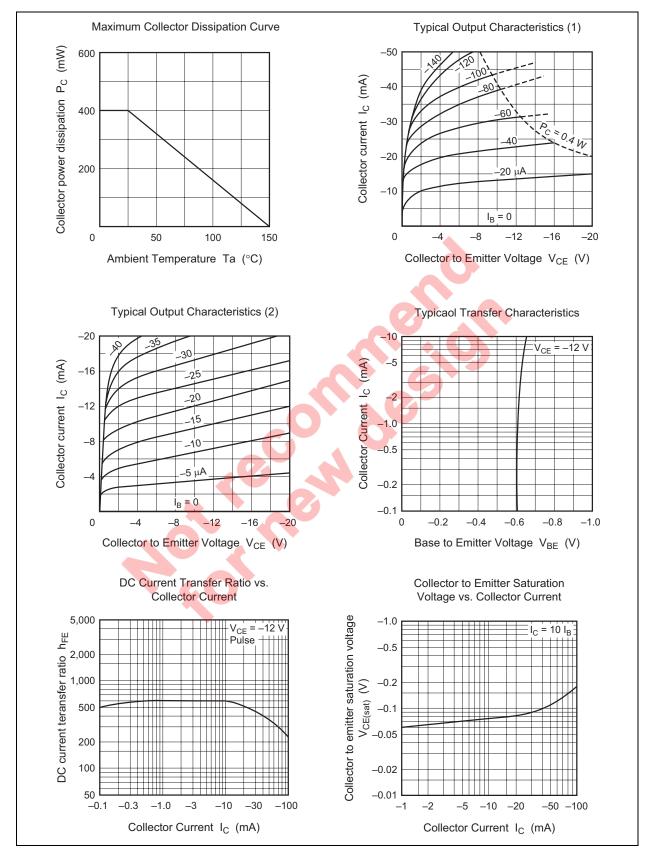
Note: 1. The 2SA1084 and 2SA1085 are grouped by h_{FE} as follows.

D E 250 to 500 400 to 800

Rev.3.00 Aug 10, 2005 page 2 of 5

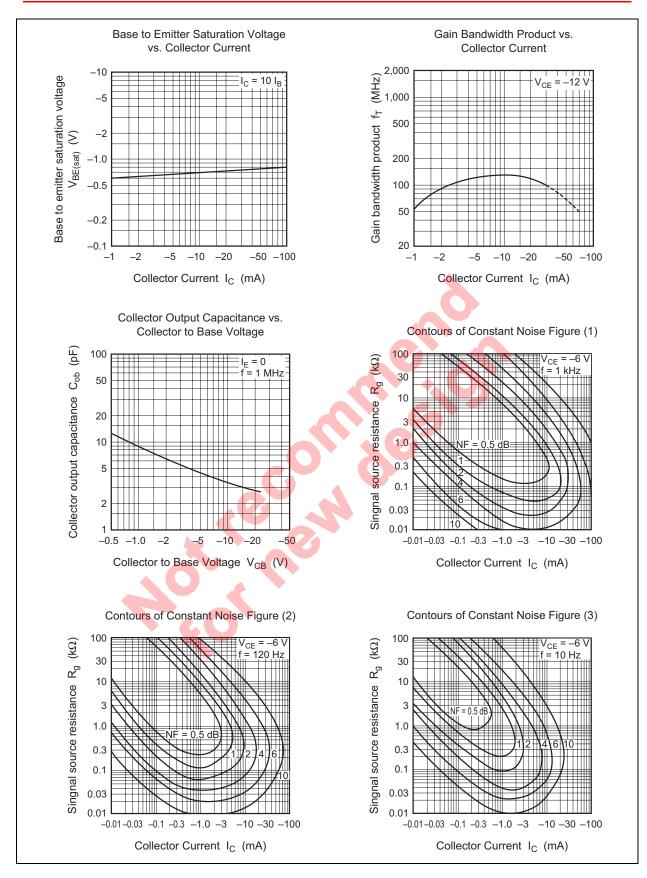


Main Characteristics



Rev.3.00 Aug 10, 2005 page 3 of 5

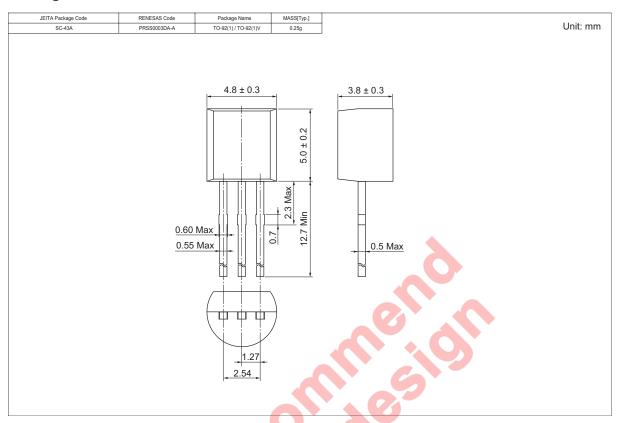




Rev.3.00 Aug 10, 2005 page 4 of 5



Package Dimensions



Ordering Information

| Part Name | Quantity | Shipping Container |
|--------------|----------|-------------------------|
| 2SA1084ETZ-E | 2500 | Hold Box, Radial Taping |
| 2SA1085DTZ-E | | |
| 2SA1085ETZ-E | | |

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.



RenesasTechnology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Keep safety first in your circuit designs! 1. Renesas Technology Corp. puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

Notes regarding these materials

- Notes regarding these materials
 1. These materials are intended as a reference to assist our customers in the selection of the Renesas Technology Corp. product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Renesas Technology Corp. or a third party.
 2. Renesas Technology Corp. assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.
 3. All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Renesas Technology Corp. or a authorized Renesas Technology Corp. product distributor for the latest product information described here may contain technical inaccuracies or typographical errors.
 Renesas Technology Corp. assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors.
 Please also pay attention to information published by Renesas Technology Corp. by various means, including the Renesas Technology Corp. Semiconductor home page (http://www.renesas.com).
 4. When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Renesas Technology Corp. assumes no responsibility for any damage, liability or other loss resulting from the information products. Renesas Technology Corp. Semiconductor no responsibility for any damage, liability or other loss resulting product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information c

- product contained nerein for any specific purposes, such as apparatus or systems for unispondition, removing the second second



RENESAS SALES OFFICES

http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

Renesas Technology America, Inc. 450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K. Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology Hong Kong Ltd. 7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.

10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.

Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510